

MOSFETs Silicon P-Channel MOS (U-MOSVI)

SSM6J808R

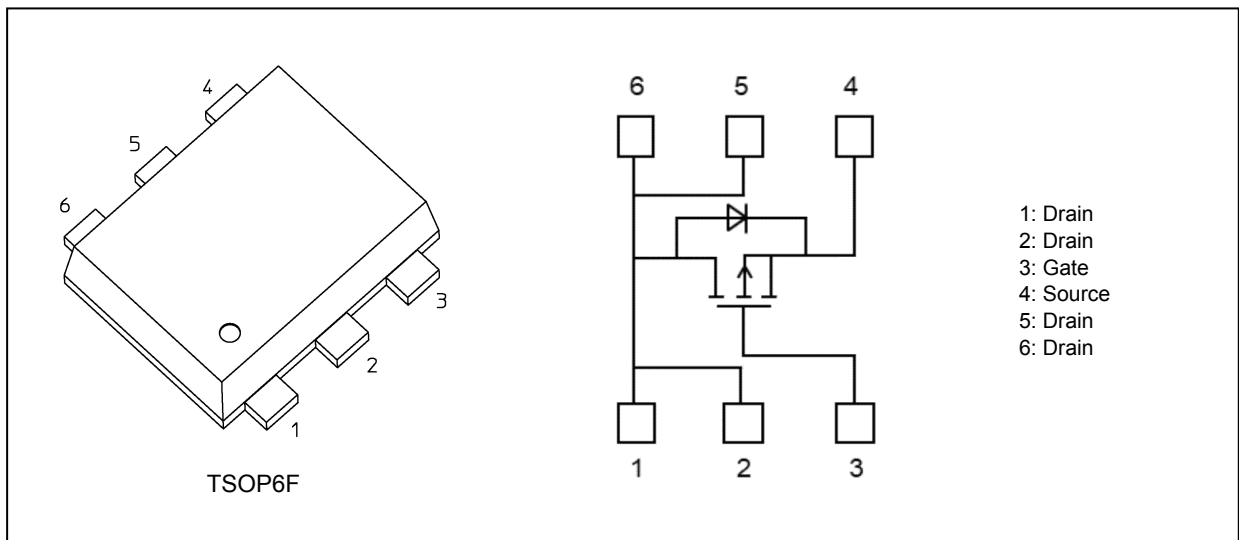
1. Applications

- Power Management Switches

2. Features

- (1) AEC-Q101 qualified
- (2) 4-V drive
- (3) Low drain-source on-resistance
 - : $R_{DS(ON)} = 28 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
 - $R_{DS(ON)} = 35 \text{ m}\Omega$ (typ.) ($V_{GS} = -4.5 \text{ V}$)
 - $R_{DS(ON)} = 38 \text{ m}\Omega$ (typ.) ($V_{GS} = -4 \text{ V}$)

3. Packaging and Internal Circuit



Start of commercial production

2019-09

4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

| Characteristics | Symbol | Rating | Unit |
|--|-----------|------------|------------------|
| Drain-source voltage | V_{DSS} | -40 | V |
| Gate-source voltage | V_{GSS} | -20/+10 | |
| Drain current (DC) (Note 1) | I_D | -7 | A |
| Drain current (pulsed) (Note 1), (Note 2) | I_{DP} | -35 | |
| Power dissipation (Note 3) | P_D | 1.5 | W |
| Power dissipation ($t < 10\text{ s}$) (Note 3) | | 3 | |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to 150 | |
| Single-pulse avalanche energy (Note 4) | E_{AS} | 40 | mJ |
| Single-pulse avalanche current | I_{AS} | -6.3 | A |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed $150\text{ }^\circ\text{C}$.

Note 2: Pulse width (PW) $\leq 10\text{ }\mu\text{s}$, duty $\leq 1\%$

Note 3: Device mounted on a $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ mm}$ FR4 glass epoxy board (Cu pad: 645 mm^2)

Note 4: $V_{DD} = -32\text{ V}$, $T_{ch} = 25\text{ }^\circ\text{C}$ (Initial state), $L = 1\text{ mH}$, $R_G = 25\text{ }\Omega$

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, P_D , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---------------|--|------|------|-----------|---------------|
| Gate leakage current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = -20/+10\text{ V}$ | — | — | ± 100 | nA |
| Drain cut-off current | I_{DSS} | $V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$ | — | — | -10 | μA |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$ | -40 | — | — | V |
| Drain-source breakdown voltage (Note 1) | $V_{(BR)DSX}$ | $I_D = -10\text{ mA}, V_{GS} = 10\text{ V}$ | -30 | — | — | |
| Gate threshold voltage | V_{th} | $V_{DS} = -10\text{ V}, I_D = -0.1\text{ mA}$ | -0.8 | — | -2 | |
| Drain-source on-resistance (Note 2) | $R_{DS(ON)}$ | $I_D = -2.5\text{ A}, V_{GS} = -4\text{ V}$ | — | 38 | 52 | m Ω |
| | | $I_D = -2.5\text{ A}, V_{GS} = -4.5\text{ V}$ | — | 35 | 48 | |
| | | $I_D = -2.5\text{ A}, V_{GS} = -10\text{ V}$ | — | 28 | 35 | |

Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------|-----------|---|-----|------|-----|------|
| Input capacitance | C_{iss} | $V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$ | — | 1020 | — | pF |
| Reverse transfer capacitance | C_{rss} | | — | 136 | — | |
| Output capacitance | C_{oss} | | — | 169 | — | |
| Switching time (turn-on time) | t_{on} | $V_{DD} = -20\text{ V}, I_D = -1\text{ A},$ $V_{GS} = 0\text{ to }-10\text{ V}, R_G = 10\text{ }\Omega$ Duty $\leq 1\%$, Input; $t_r, t_f < 5\text{ ns}$ Ground source, See 5.3 | — | 32 | — | ns |
| Switching time (turn-off time) | t_{off} | | — | 151 | — | |

5.3. Switching Time Test Circuit

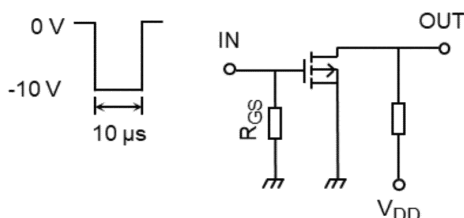


Fig. 5.3.1 Switching Time Test Circuit

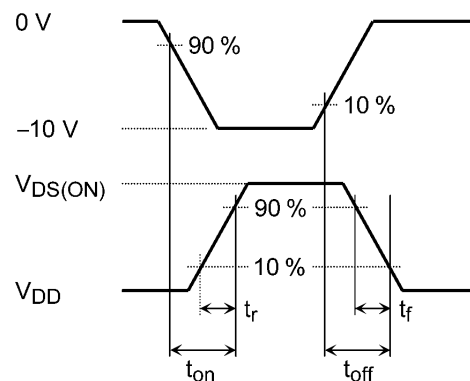


Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

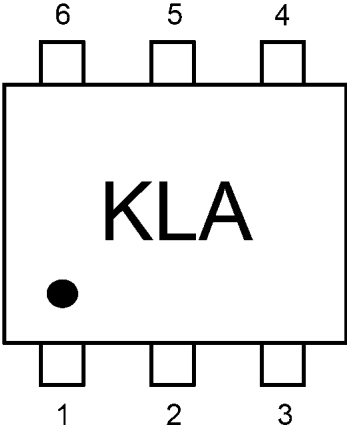
| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|-----------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Q_g | $V_{DD} = -32\text{ V}, I_D = -5\text{ A},$ $V_{GS} = -10\text{ V}$ | — | 24.2 | — | nC |
| Gate-source charge 1 | Q_{gs1} | | — | 3 | — | |
| Gate-drain charge | Q_{gd} | | — | 5.3 | — | |

5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25\text{ }^\circ\text{C}$)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------|-----------|---|-----|------|-----|------|
| Diode forward voltage (Note 1) | V_{DSF} | $I_D = 7\text{ A}, V_{GS} = 0\text{ V}$ | — | 0.86 | 1.2 | V |

Note 1: Pulse measurement.

6. Marking



7. Characteristics Curves (Note)

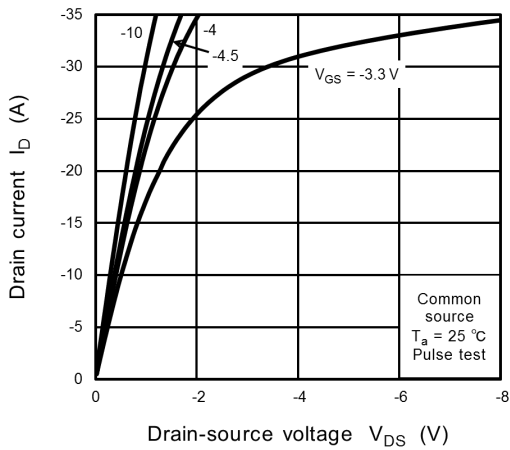


Fig. 7.1 $I_D - V_{DS}$

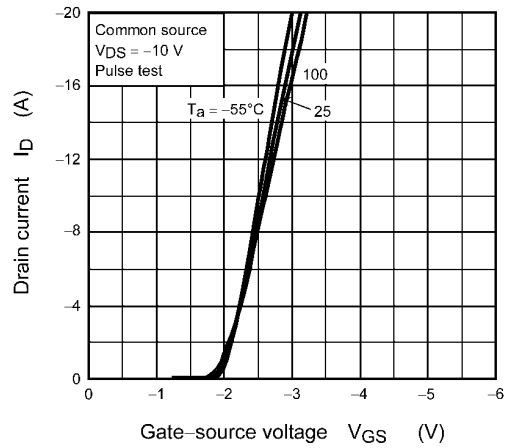


Fig. 7.2 $I_D - V_{GS}$

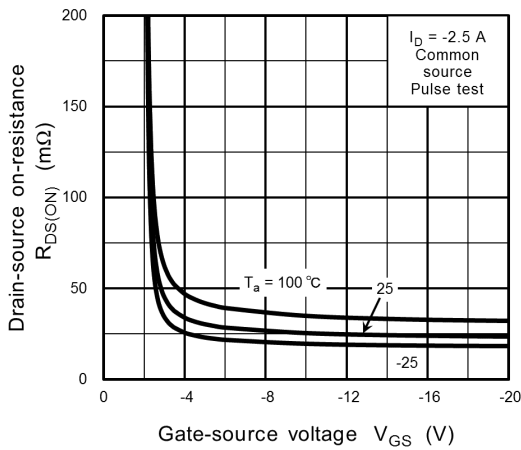


Fig. 7.3 $R_{DS(ON)} - V_{GS}$

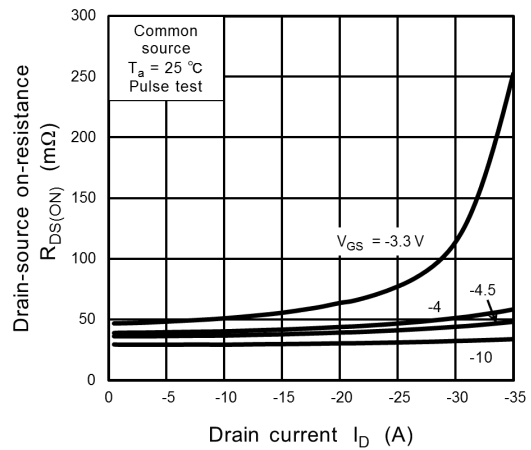


Fig. 7.4 $R_{DS(ON)} - I_D$

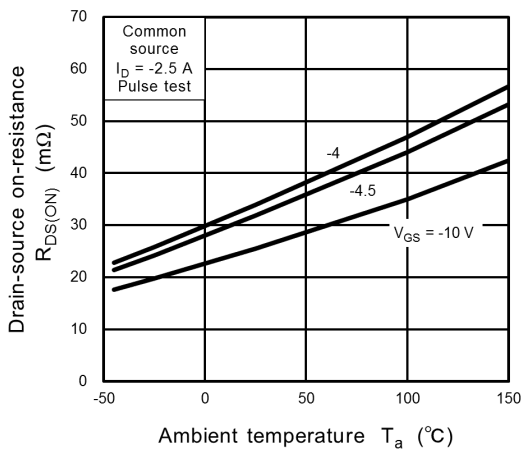


Fig. 7.5 $R_{DS(ON)} - T_a$

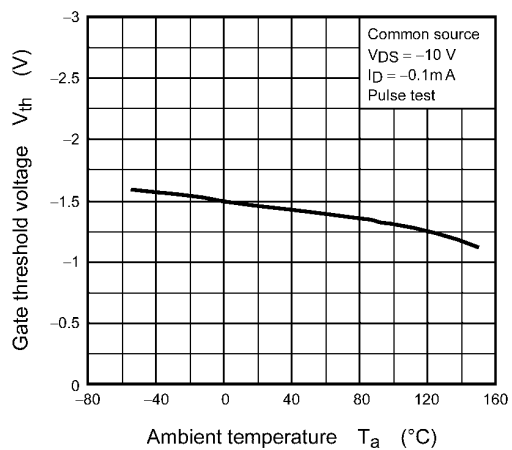


Fig. 7.6 $V_{th} - T_a$

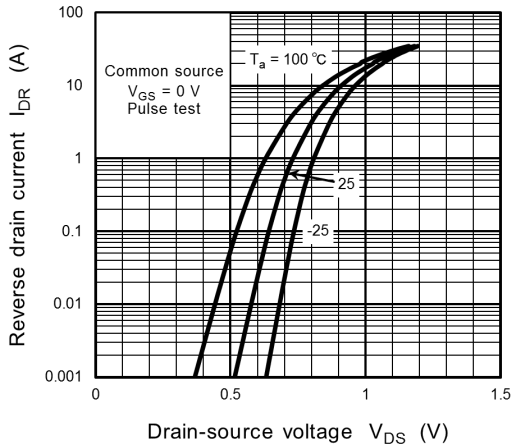


Fig. 7.7 $I_{DR} - V_{DS}$

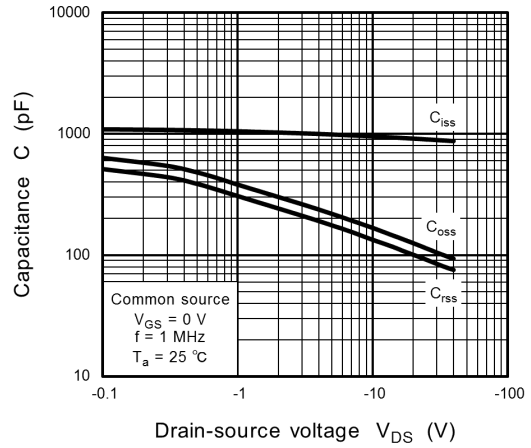


Fig. 7.8 $C - V_{DS}$

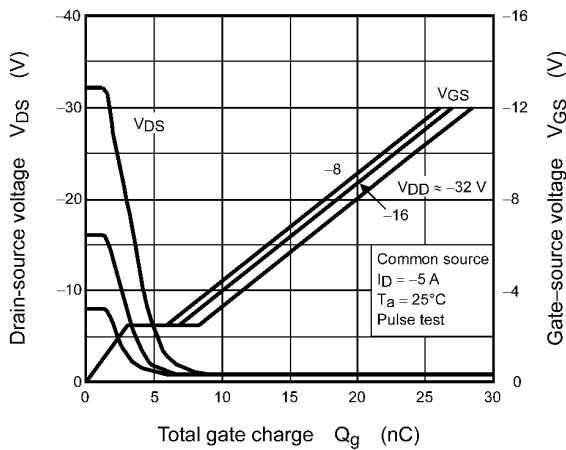


Fig. 7.9 Dynamic Input Characteristics

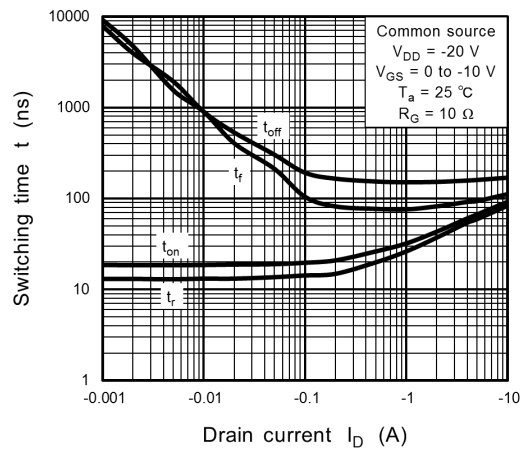


Fig. 7.10 $t - I_D$

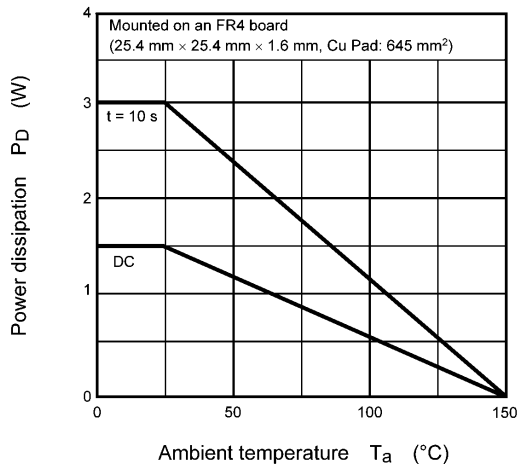
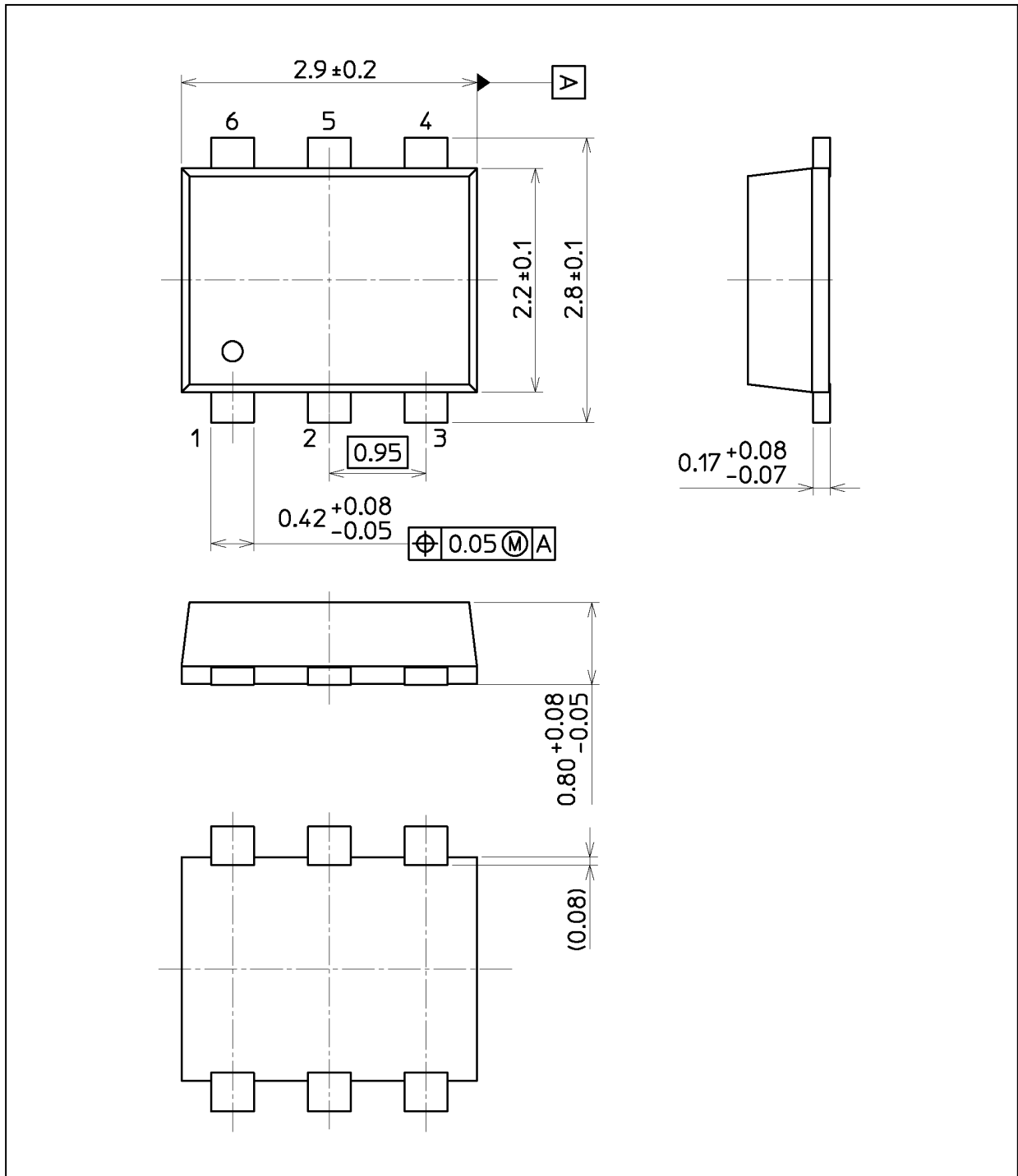


Fig. 7.11 $P_D - T_a$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.016 g (typ.)

| |
|------------------|
| Package Name(s) |
| Nickname: TSOP6F |

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